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2227/323 (2013.01)

(57) **ABSTRACT**

An OLED substrate (1) and a preparation method therefor, an OLED panel, and an OLED display apparatus. An inter-layer insulation layer (12) is formed in an edge area of the OLED substrate (1), and a concave is formed on the surface of the inter-layer insulation layer (12), so that the lateral tensile-resistance strength of the inter-layer insulation layer (12) and a package substrate can be increased, i.e. increasing a lateral tensile-resistance force between the OLED substrate (1) and the package substrate, thereby improving the stability of the OLED panel, ensuring the sealing effect of the OLED panel and improving the service life of the OLED panel.

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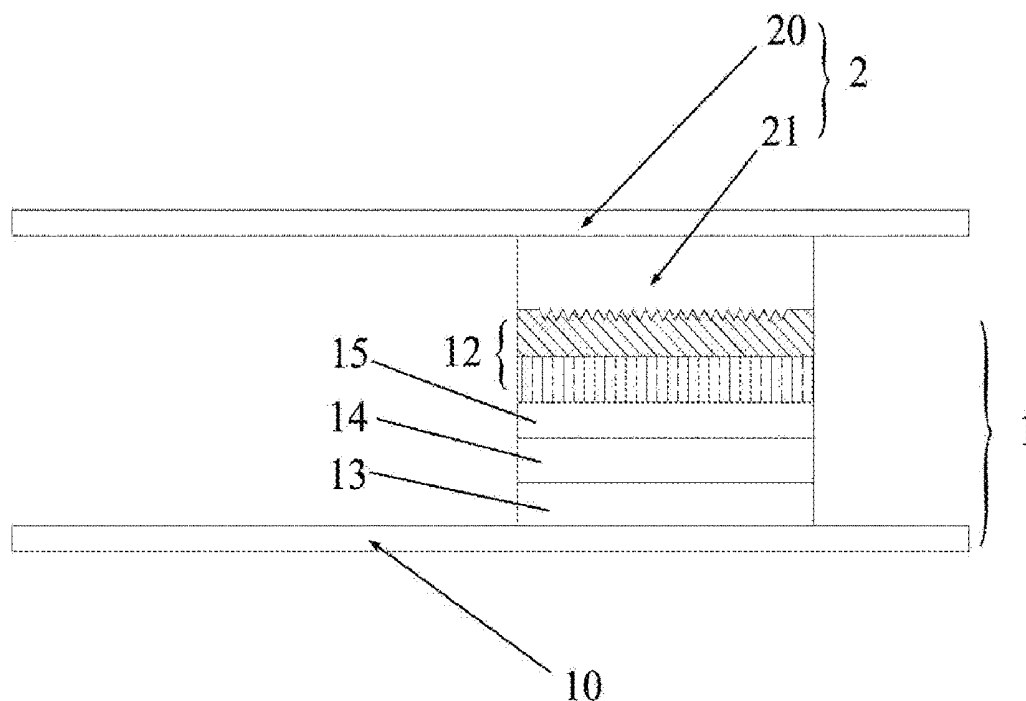
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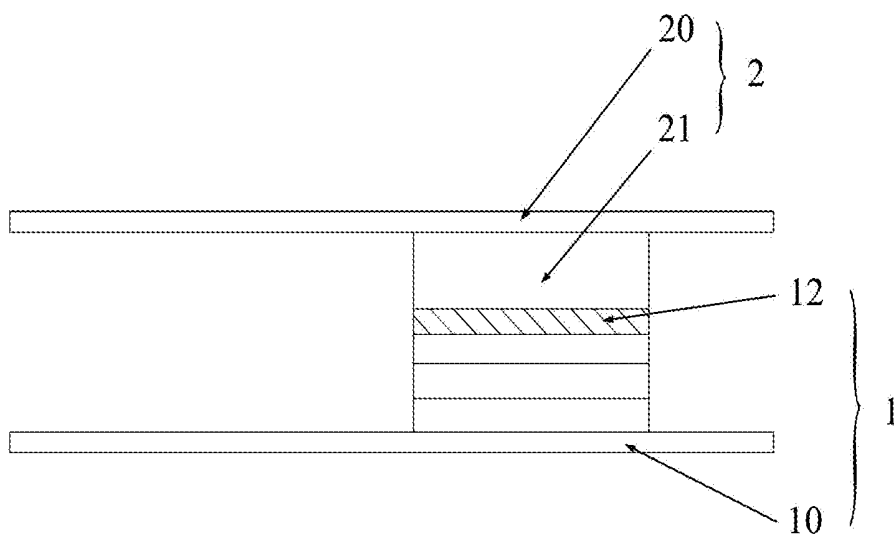


FIG. 1

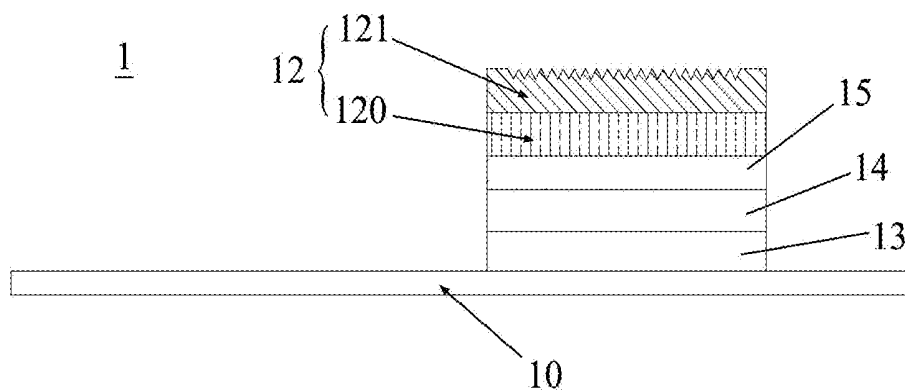


FIG. 2

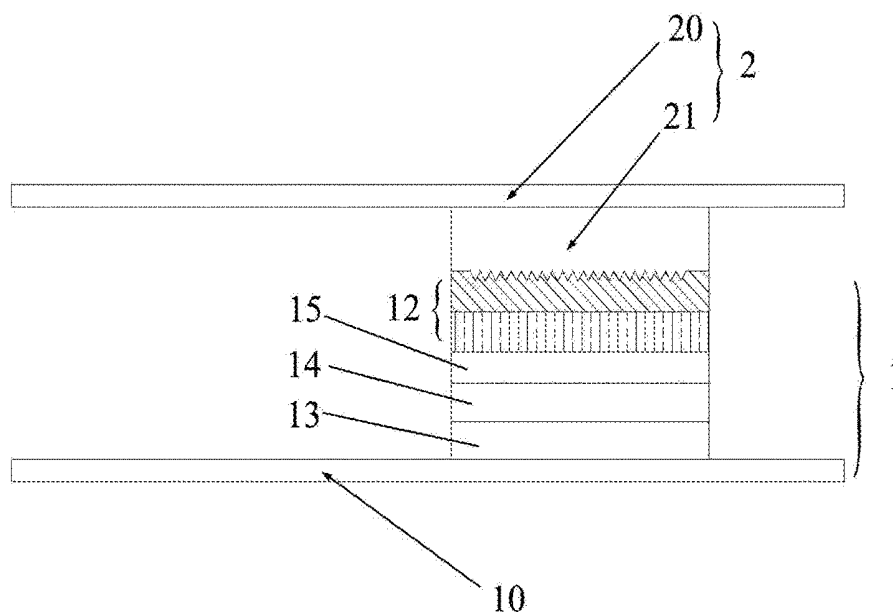


FIG. 3

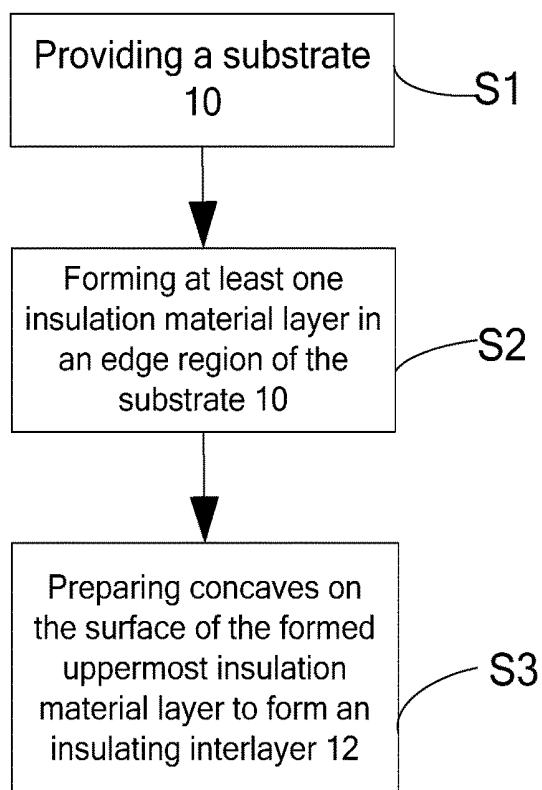


FIG. 4

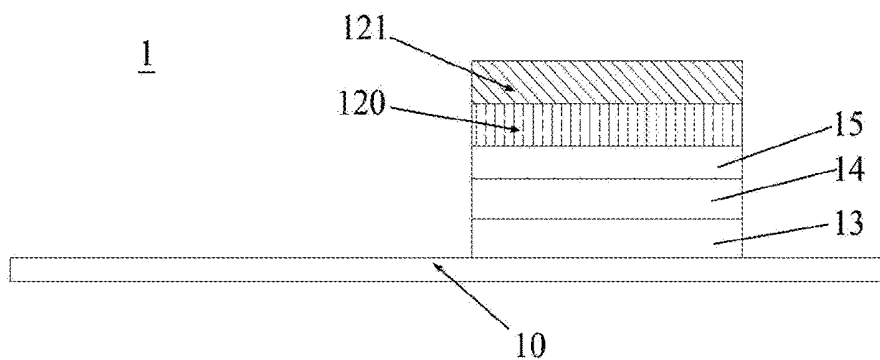


FIG 5

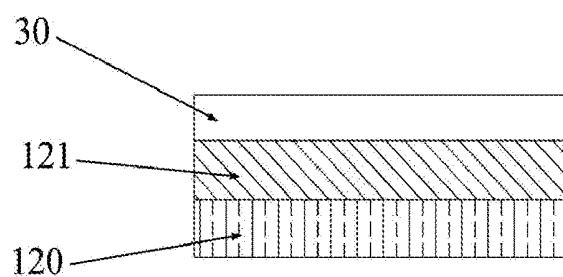


FIG 6

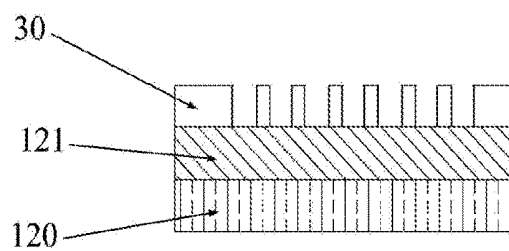


FIG 7

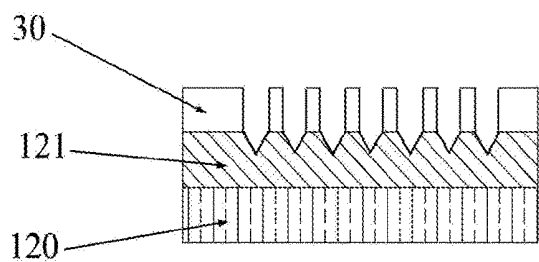


FIG 8

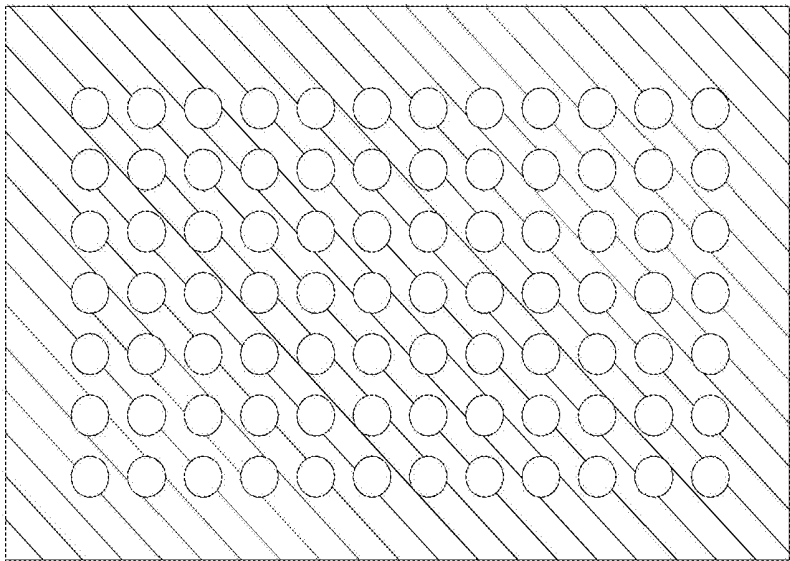


FIG. 9

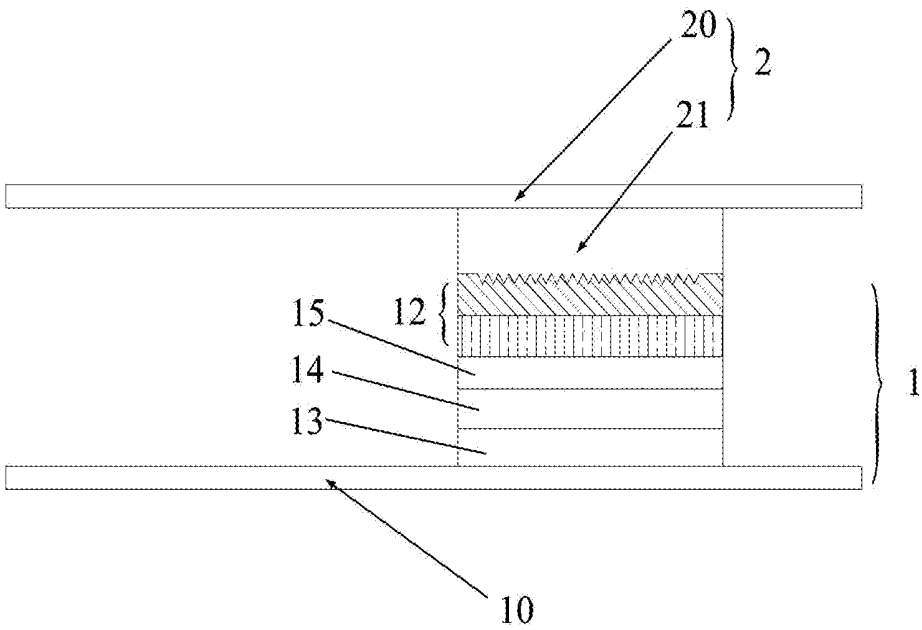


FIG. 10

OLED SUBSTRATE AND PREPARATION METHOD THEREOF, OLED PANEL, AND DISPLAY APPARATUS

TECHNICAL FIELD

[0001] The present disclosure relates to a technical field of display, in particular to an OLED substrate and a preparation method thereof, an OLED panel and an OLED display device.

BACKGROUND

[0002] A package sealing effect of an OLED device directly affects a service life of the OLED device, and therefore, it is an important index for evaluating quality of the OLED device.

[0003] FIG. 1 is a schematic diagram of part of a structure of a conventional OLED panel. As shown in FIG. 1, the OLED panel is formed by cell-assembling an OLED substrate 1 and a package substrate 2. The OLED substrate 1 comprises a substrate 10 and a light-emitting structure (including an anode layer, a cathode layer, and an organic function layer, etc.) prepared on the substrate 10. In an edge region of the OLED substrate 1, an insulating interlayer (ILD) 12 is further disposed, and the insulating interlayer 12 is located on an outermost side of the OLED substrate 1. The package substrate 2 comprises a glass layer 20 and glass cement 21 prepared in an edge region of the glass layer 20. When the OLED substrate 1 and the package substrate 2 are cell-assembled, the glass cement 21 and the insulating interlayer 12 are jointed, and the glass cement 21 is melted by laser irradiation, such that the OLED substrate 1 and the package substrate 2 are bonded together.

[0004] In practice, a transverse strength between the glass cement 21 and the insulating interlayer 12 is relatively small, such that it is hard for the OLED panel to bear a larger transverse pull force (i.e., a force in a direction parallel to the substrate 10 and the glass layer 20). When the transverse pull force is relatively large, relative movement emerges between the OLED substrate 1 and the package substrate 2 in the above OLED panel, as a result, a sealing effect of the OLED panel becomes poorer and the service life of the OLED panel is affected.

SUMMARY

[0005] In order to solve the above problems in the conventional technical solutions, embodiments of the present invention provide an OLED substrate and a preparation method therefor, an OLED panel and an OLED display apparatus. The lateral tensile-resistance strength of the insulating interlayer and a package substrate can be increased, i.e. increasing a lateral tensile-resistance force between the OLED substrate and the package substrate, thereby improving the stability of the OLED panel, ensuring the sealing effect of the OLED panel and improving the service life of the OLED panel.

[0006] Embodiments of the present invention provide an OLED substrate, wherein, an insulating interlayer is disposed in an edge region of the OLED substrate, at least one concave is provided on a surface of the insulating interlayer.

[0007] In one embodiment of the present invention, for example, the insulating interlayer comprises at least one layer of insulation material.

[0008] In one embodiment of the present invention, for example, a depth of the concave is not greater than 20% of a thickness of the insulating interlayer.

[0009] In one embodiment of the present invention, for example, at least two concaves are provided on a surface of the insulating interlayer and edges of adjacent concaves are connected to each other.

[0010] In one embodiment of the present invention, for example, at least two concaves is provided on a surface of the insulating interlayer and at least two concaves are uniformly distributed on the surface of the insulating interlayer.

[0011] In one embodiment of the present invention, for example, the insulating interlayer and an insulating layer over a gate electrode layer in a display region of the OLED substrate are disposed in a same layer.

[0012] In one embodiment of the present invention, for example, the edge region of the OLED substrate further comprises at least one of an active layer, a gate insulating layer and a gate electrode layer formed below the insulating interlayer.

[0013] In one embodiment of the present invention, for example, the active layer, the gate insulating layer and/or the gate electrode layer in the edge region of the OLED substrate are respectively disposed in a same layer as an active layer, a gate insulating layer and/or a gate electrode layer in a thin film transistor circuit of the OLED substrate.

[0014] Embodiments of the present invention provide a method for preparing an OLED substrate, comprising: providing a substrate; forming at least one insulation material layer in an edge region of the substrate; and preparing a concave on a surface of the at least one insulation material layer to form an insulating interlayer.

[0015] In one embodiment of the present invention, for example, in the method, prior to the preparing the concave, the at least one insulation material layer and an insulating layer over a gate electrode layer in a display region of the OLED substrate are formed simultaneously.

[0016] In one embodiment of the present invention, for example, in the method, the concave is formed by a photoetching process.

[0017] In one embodiment of the present invention, for example, in the method, when an insulating layer over a gate electrode layer in a display region of the OLED substrate is formed, the insulating interlayer having the concave on the surface is formed by a semi-exposure process.

[0018] In one embodiment of the present invention, for example, in the method, a depth of the concave is not greater than 20% of a total thickness of the at least one insulation material layer.

[0019] In one embodiment of the present invention, for example, in the method, prior to the forming the at least one insulation material layer, the method further comprises: forming at least one of an active layer, a gate insulating layer and a gate electrode layer in the edge region of the substrate.

[0020] In one embodiment of the present invention, for example, in the method, an active layer, a gate insulating layer and/or a gate electrode layer in a thin film transistor circuit of the OLED substrate are formed simultaneously with the forming of the active layer, the gate insulating layer and/or the gate electrode layer in the edge region of the substrate.

[0021] Embodiments of the present invention provide an OLED panel, comprising the above described OLED substrate.

[0022] In the OLED substrate and the preparation method thereof, the OLED panel and the OLED display apparatus provided by the embodiments of the present invention, concaves are provided on the surface of the insulating interlayer; when the OLED substrate and the package substrate are cell-assembled to be packaged, the glass cement of the package substrate can be embedded into the insulating interlayer through the concaves, such that the glass cement and the insulating interlayer are combined together; in this way, a lateral tensile-resistance strength of the inter-layer insulating layer and a package substrate can be increased, i.e. increasing a lateral tensile-resistance force between the OLED substrate and the package substrate, thereby improving the stability of the OLED panel, ensuring the sealing effect of the OLED panel and improving the service life of the OLED panel.

BRIEF DESCRIPTION OF THE DRAWINGS

[0023] The drawings constituting part of the specification are used to further explain the present disclosure, and are used for explaining the present disclosure together with specific embodiments below rather than limiting the present disclosure.

[0024] FIG. 1 is a schematic diagram of part of a structure of an conventional OLED panel;

[0025] FIG. 2 is a schematic diagram of part of a structure of an OLED substrate according to an embodiment of the present disclosure;

[0026] FIG. 3 is a schematic diagram of part of a structure after an OLED substrate and a package substrate are cell-assembled according to an embodiment of the present disclosure;

[0027] FIG. 4 is a flow chart showing the preparing process of an insulating interlayer according to an embodiment of the present disclosure;

[0028] FIG. 5 is a schematic diagram of an edge structure of an OLED substrate after an insulation material layer is prepared according to an embodiment of the present disclosure;

[0029] FIG. 6 is a schematic diagram of an edge structure of an OLED substrate after the insulation material layer is coated with photoresist according to an embodiment of the present disclosure;

[0030] FIG. 7 is a schematic diagram of an edge structure of an OLED substrate after exposing and developing according to an embodiment of the present disclosure;

[0031] FIG. 8 is a schematic diagram of an edge structure of an OLED substrate after etching according to an embodiment of the present disclosure;

[0032] FIG. 9 is a schematic diagram of a mask used when the structure of an insulating interlayer is manufactured according to an embodiment of the present disclosure; and

[0033] FIG. 10 is a schematic diagram of part of a structure of an OLED panel according to an embodiment of the present disclosure.

DETAILED DESCRIPTION

[0034] The technical solutions of the embodiment will be described in a clearly and fully understandable way in connection with the drawings related to the embodiments of

the disclosure. It is understandable that the described embodiments are just exemplary embodiments for explaining the present invention. The present invention is not limited by the above described embodiments.

[0035] An embodiment of the present disclosure provides an OLED substrate, and FIG. 2 is a schematic diagram of part of structure of an OLED substrate provided by an embodiment of the present disclosure. In the present embodiment, as shown in FIG. 2, the OLED substrate comprises a substrate 10 and an insulating interlayer 12 disposed in an edge region of the OLED substrate 1, and at least one concave is provided on a surface of the insulating interlayer 12.

[0036] FIG. 3 is a schematic diagram of part of an OLED structure after the substrate 1 and the package substrate 2 are cell-assembled according to an embodiment of the present disclosure. As shown in FIG. 3, the package substrate 2 comprises a glass layer 20 and glass cement 21 disposed in the edge region of the package substrate 2.

[0037] With reference to FIG. 2 and FIG. 3, concaves are provided on the surface of the insulating interlayer 12; when the OLED substrate 1 and the package substrate 2 are cell-assembled to be packaged, the glass cement 21 of the package substrate 2 can be embedded into the insulating interlayer 12 through the concaves, such that the glass cement 21 and the insulating interlayer 12 are combined together; in this way, a lateral tensile-resistance strength of the inter-layer insulating layer 12 and a package substrate can be increased, i.e. increasing a lateral tensile-resistance force between the OLED substrate 1 and the package substrate 2, thereby improving the stability of the OLED panel, ensuring the sealing effect of the OLED panel and improving the service life of the OLED panel.

[0038] In the present embodiment, the insulating interlayer 12 comprises at least one insulation material layer. For example, as shown in FIG. 2, the insulating interlayer 12 comprises two insulation material layers 120 and 121, the insulation material layer 120 is made of SiO_x and the insulation material layer 121 is made of SiN_x .

[0039] In the present embodiment, for example, a depth of the concave is not greater than 20% of a thickness of the insulating interlayer. In this way, the concave has a certain depth, such that the lateral tensile-resistance strength between the insulating interlayer 12 and the glass cement 21 is ensured, meanwhile it is ensured that the insulating interlayer 12 has enough thickness at the positions corresponding to the concaves, and a good insulation effect is realized.

[0040] In the present embodiment, a plurality of the concaves can be provided. On this basis, the edges of the adjacent concaves can be connected mutually, that is, the plurality of concaves form a "sawtooth" shape; in this way, the lateral tensile-resistance strength between the insulating interlayer 12 and the glass cement 21 is increased to the greatest extent, and the stability of the OLED panel is improved.

[0041] In addition, in a case that the number of the concaves is plural, the plurality of concaves can be uniformly distributed on the surface of the insulating interlayer 12; due to such setting, each region of the insulating interlayer 12 and the glass cement 21 can bear a friction force uniformly.

[0042] The insulating interlayer 12 and an insulating layer over a gate electrode layer in a display region are disposed

in a same layer, and the edge region of the OLED substrate **1** further comprises at least one of an active layer **13**, a gate insulating layer **14** and a gate electrode layer **15** formed below the insulating interlayer **12**.

[0043] It is appreciated that in the present disclosure, “disposed in a same layer” means “formed in a same patterning process”, that is, formed in one patterning process with a same mask.

[0044] A thin film transistor circuit is manufactured in the display region of the OLED substrate **1**, that is, structures such as the active layer, the gate insulating layer, the gate electrode layer, the insulating interlayer, an S/D layer and the like are formed in sequence. In the present embodiment, the active layer **13**, the gate insulating layer **14** and/or the gate electrode layer **15** in the edge region of the OLED substrate **1** and the active layer, the gate insulating layer and/or the gate electrode layer in the thin film transistor circuit of the OLED substrate **1** are formed at the same time; that is, when the active layer, the gate insulating layer and/or the gate electrode layer in the circuit of the OLED substrate **1** are formed, structures of the active layer **13**, the gate insulating layer **14** and/or the gate electrode **15** are reserved in the edge region of the OLED substrate **1** instead of being etched; in this way, the insulating interlayer **12** in the edge region of the OLED substrate **1** is heightened, that is, the insulating interlayer **12** is prepared at a higher position on the surface of the substrate **10** to be conveniently combined with the glass cement **21**. For example, in one embodiment, as shown in FIG. 2, the active layer **13**, the gate electrode layer **14** and the gate electrode layer **15** are disposed below the insulating interlayer **12**.

[0045] In conclusion, in the OLED substrate **1** provided by the embodiments of the present disclosure, the concaves are provided on the surface of the insulating interlayer **12**; when the OLED substrate **1** and the package substrate **2** are cell-assembled to be packaged, the insulating interlayer **12** and the glass cement **21** of the package substrate **2** can be combined together through the concaves; in this way, a lateral tensile-resistance strength of the inter-layer insulating layer **12** and a package substrate can be increased, i.e. increasing a lateral tensile-resistance force between the OLED substrate **1** and the package substrate **2**, thereby improving the stability of the OLED panel, ensuring the sealing effect of the OLED panel and improving the service life of the OLED panel.

[0046] Another embodiment of the present disclosure provides a method for preparing an OLED substrate, and FIG. 4 is a flow chart of a method for preparing an OLED substrate provided by an embodiment of the present disclosure. As shown in FIG. 4, the method for preparing an OLED substrate comprises the following steps S1-S3.

[0047] In step S1, providing a substrate **10**.

[0048] In step S2, forming at least one insulation material layer in an edge region of the substrate **10**, as shown in FIG. 5.

[0049] For example, the material of the insulation material layer can be SiO_x , SiN_x or other insulation materials. For example, as shown in FIG. 5, SiO_x and SiN_x are deposited in sequence, such that the two insulation material layers **120** and **121**, that is, a SiO_x layer and a SiN_x layer are obtained on the substrate **1**.

[0050] In addition, while the insulating layer over the gate electrode layer in a display region of the OLED substrate is formed, at least one insulation material layer is formed in the

edge region of the substrate **10**, that is, the insulating layer over the gate electrode layer in the display region of the OLED substrate and the at least one insulation material layer can be formed in a same patterning process.

[0051] In step S3, preparing concaves on the surface of the formed uppermost insulation material layer to form an insulating interlayer **12**, as shown in FIG. 2. For example, after the insulation material layers **120** and **121** as shown in FIG. 5 are deposited, the concaves are prepared on the surface of the SiN_x layer **121**.

[0052] The concaves can be prepared through a photoetching process. For example, the photoetching process for preparing the concaves may comprise the following steps S30-S33.

[0053] In step S30, coating a surface of the uppermost insulation material layer with photoresist **30**, as shown in FIG. 6. The photoresist **30** may be positive or negative photoresist.

[0054] In step S31, exposing and developing the photoresist **30** as shown in FIG. 7.

[0055] In step S32, forming the concaves on the surface of the uppermost insulation material layer, as shown in FIG. 8.

[0056] For example, after each part of the photoresist **30** is removed, the exposed regions of the insulation material layers are all round, and round concaves can be obtained by the etching process in step S32. For example, in order to obtain the round exposed regions of the insulation material layers, in a case that the photoresist layer **30** is positive photoresist, a mask used for exposing the photoresist **30** is provided to have a round transparent region, as shown in FIG. 9; and in a case that the photoresist **30** is negative photoresist, a mask used by exposing the photoresist **30** is provided to have a round opaque region.

[0057] In step S33, stripping off residual photoresist **30** on the surface of the insulation material layer, and obtaining the insulating interlayer **12** as shown in FIG. 2.

[0058] The insulating interlayer **12** prepared according to the above described processes has the concaves on the surface. When the OLED substrate and the package substrate **2** are cell-assembled for packaging, the glass cement **21** of the package substrate **2** can be embedded into the insulating interlayer **12** through the concaves, such that the glass cement **21** and the insulating interlayer **12** can be combined together; in this way, a lateral tensile-resistance strength of the inter-layer insulating layer **12** and a package substrate can be increased, i.e. increasing a lateral tensile-resistance force between the OLED substrate **1** and the package substrate **2**, thereby improving the stability of the OLED panel, ensuring the sealing effect of the OLED panel and improving the service life of the OLED panel.

[0059] In the present embodiment, for example, an etching depth in the etching process is not greater than 20% of a total thickness of the insulation material layer. For example, in the example as shown in FIG. 2, the depth of the concaves is not greater than 20% of a sum of thicknesses of the SiO_x layer **120** and the SiN_x layer **121**. Due to such setting, the concaves can have certain depth, such that the lateral tensile-resistance strength between the insulating interlayer **12** and the glass cement **21** is ensured, meanwhile it is ensured that the insulating interlayer **12** has enough thickness at the positions corresponding to the concaves, and a good insulation effect is realized.

[0060] In the present embodiment, for example, a plurality of concaves are formed on the surface of the insulation

material layer, and the edges of the adjacent concaves can be connected mutually, that is, the multiple concaves form a “sawtooth” shape; in this way, the lateral tensile-resistance strength between the insulating interlayer 12 and the glass cement 21 is increased to the greatest extent, and the stability of the OLED panel is improved.

[0061] Meanwhile, in a case that a plurality of concaves are formed on the surface of the insulation material layer, the plurality of concaves can be uniformly distributed on the insulation material layer, and due to such setting, each region of the insulating interlayer 12 and the glass cement 21 can bear a friction force uniformly.

[0062] For example, at least one of an active layer 13, a gate insulating layer 14 and a gate electrode 15 is formed below the insulating interlayer 12. The active layer 13, the gate insulating layer 14 and/or the gate electrode layer 15 and the active layer, the gate insulating layer and/or the gate electrode layer in the circuit of the OLED substrate are formed at the same time; that is, when the active layer, the gate insulating layer and/or the gate electrode layer in the circuit of the OLED substrate 1 are formed, structures of the active layer, 13, the gate insulating layer 14 and/or the gate electrode layer 15 are reserved in the edge region of the OLED substrate instead of being etched; in this way, the insulating interlayer 12 is heightened, that is, the insulating interlayer 12 is prepared at a higher position of the substrate 20, to be conveniently combined with the glass cement 21.

[0063] It is noted that in the present embodiment, when an insulating layer above the gate electrode layer in the display region is formed, the insulating interlayer 12 having the concaves may be formed through a semi-exposure process at the same time. Compared with the above described method, process configuration can be reduced in this way, such that production time is reduced and production efficiency is improved.

[0064] Another embodiment of the present disclosure provides an OLED panel, and FIG. 10 is a schematic diagram of part of a structure of an OLED panel provided by an embodiment of the present disclosure. In the present embodiment, as shown in FIG. 10, the OLED panel comprises the OLED substrate 1 and the package substrate 2 provided by the embodiments of the present disclosure, the OLED substrate 1 contacts the package substrate 2 through a surface of the insulating interlayer 12, the package substrate 2 contacts the OLED substrate 1 through a surface of the glass cement 21, the insulating interlayer 12 and the glass cement 21 are fused together, and the surface of the insulating interlayer 12 has concaves.

[0065] In the OLED panel provided by the embodiment of the present disclosure, the surface of the insulating interlayer 12 has concaves, such that the OLED substrate 1 and the glass cement 21 of the package substrate 2 are combined together through the concaves; in this way, a lateral tensile-resistance strength of the inter-layer insulating layer 12 and a package substrate can be increased, i.e. increasing a lateral tensile-resistance force between the OLED substrate 1 and the package substrate 2, thereby improving the stability of the OLED panel, ensuring the sealing effect of the OLED panel and improving the service life of the OLED panel.

[0066] Another embodiment of the present disclosure provides an OLED display device. In the present embodiment, the OLED display device comprises the OLED panel provided by the embodiment of the present disclosure.

[0067] In the OLED display device provided by the embodiment of the present disclosure, the transverse tensile resistance of the OLED panel is increased, such that the OLED panel of the OLED display device has better stability and sealing effect, and the service life of the OLED display device is prolonged.

[0068] It is noted that in the drawings, although the active layer 13, the gate insulating layer 14 and/or the gate electrode layer 15 are disposed or formed on the substrate 10 below the insulating interlayer 12 in sequence, but the present disclosure is not limited thereto. In other embodiments of the present disclosure, below the insulating interlayer 12, the gate electrode layer 15, the gate insulating layer 14 and/or the active layer 13 can be disposed or formed below the insulating interlayer 12 in sequence as long as the electrode layer 15, the gate insulating layer 14 and/or the active layer 13 heighten the insulating layer 1. In addition, the terms “and/or” refer to any of listed respective elements.

[0069] It is understandable that the above described embodiments are just exemplary embodiments for explaining the principle of the present invention. The present invention are not limited by the above described embodiments. Based on the described embodiments herein, those skilled in the art can obtain other embodiment(s), without any inventive work, which should be within the scope of the disclosure.

[0070] The present application claims the priority of the Chinese Patent Application No. 201510119584.9 filed on Mar. 18, 2015, which is incorporated herein by reference as part of the disclosure of the present application.

1. An organic light emitting diode (OLED) substrate, wherein, an insulating interlayer is disposed in an edge region of the OLED substrate, and at least one concave is provided on a surface of the insulating interlayer.

2. The OLED substrate according to claim 1, wherein the insulating interlayer comprises at least one layer of insulation material.

3. The OLED substrate according to claim 1, wherein a depth of the concave is not greater than 20% of a thickness of the insulating interlayer.

4. The OLED substrate according to claim 1, wherein at least two concaves are provided on a surface of the insulating interlayer and edges of adjacent concaves are connected to each other.

5. The OLED substrate according to claim 1, wherein at least two concaves are provided on a surface of the insulating interlayer and at least two concaves are uniformly distributed on the surface of the insulating interlayer.

6. The OLED substrate according to claim 1, wherein the insulating interlayer and an insulating layer over a gate electrode layer in a display region of the OLED substrate are disposed in a same layer.

7. The OLED substrate according to claim 1, wherein the edge region of the OLED substrate further comprises at least one of an active layer, a gate insulating layer and a gate electrode layer formed below the insulating interlayer.

8. The OLED substrate according to claim 7, wherein the active layer, the gate insulating layer and/or the gate electrode layer in the edge region of the OLED substrate are respectively disposed in a same layer as an active layer, a gate insulating layer and/or a gate electrode layer in a thin film transistor circuit of the OLED substrate.

9. A method for preparing an organic light-emitting diode (OLED) substrate, comprising:

providing a substrate;
forming at least one insulation material layer in an edge region of the substrate; and
preparing a concave on a surface of the at least one insulation material layer to form an insulating interlayer.

10. The method according to claim 9, wherein prior to the preparing the concave, the at least one insulation material layer and an insulating layer over a gate electrode layer in a display region of the OLED substrate are formed simultaneously.

11. The method according to claim 9, wherein the concave is formed by a photoetching process.

12. The method according to claim 10, wherein when an insulating layer over a gate electrode layer in a display region of the OLED substrate is formed, the insulating interlayer having the concave on the surface is formed by a semi-exposure process.

13. The method according to claim 9, wherein a depth of the concave is not greater than 20% of a total thickness of the at least one insulation material layer.

14. The method according to claim 9, wherein prior to the forming the at least one insulation material layer, the method further comprises:

forming at least one of an active layer, a gate insulating layer and a gate electrode layer in the edge region of the substrate.

15. The method according to claim 14, wherein an active layer, a gate insulating layer and/or a gate electrode layer in a thin film transistor circuit of the OLED substrate are formed simultaneously with forming of the active layer, the gate insulating layer and/or the gate electrode layer in the edge region of the substrate.

16. An organic light-emitting diode (OLED) panel, comprising the OLED substrate according to claim 1.

17. The OLED panel according to claim 16, further comprising a package substrate, wherein glass cement is formed in an edge region of the package substrate, wherein the surface of the insulating interlayer having the concave are bonded together with the glass cement.

18. An organic light-emitting diode (OLED) display device, comprising the OLED panel according to claim 16.

19. An organic light-emitting diode (OLED) panel, comprising the OLED substrate according to claim 2.

20. An organic light-emitting diode (OLED) panel, comprising the OLED substrate according to claim 3.

* * * * *

专利名称(译)	OLED基板及其制备方法，OLED面板和显示装置		
公开(公告)号	US20170288165A1	公开(公告)日	2017-10-05
申请号	US15/507044	申请日	2015-09-18
[标]申请(专利权)人(译)	京东方科技集团股份有限公司 鄂尔多斯市源盛光电有限责任公司		
申请(专利权)人(译)	京东方科技集团股份有限公司. 鄂尔多斯源盛光电有限公司.		
当前申请(专利权)人(译)	京东方科技集团股份有限公司. 鄂尔多斯源盛光电有限公司.		
[标]发明人	AO NING BAI NINI ZHANG CHAOBO		
发明人	AO, NING BAI, NINI ZHANG, CHAOBO		
IPC分类号	H01L51/52 H01L27/32 H01L51/00		
CPC分类号	H01L51/5237 H01L2227/323 H01L27/3262 H01L51/0096 H01L27/3244 H01L51/5246 H01L51/5253		
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外部链接	Espacenet USPTO		

摘要(译)

OLED基板 (1) 及其制备方法，OLED面板和OLED显示装置。在 OLED基板的边缘区域 (1) 中形成层间绝缘层 (12)，并且在层间的表面上形成凹陷绝缘层 (12)，使得层间绝缘层 (12) 和封装基板的横向抗拉强度可以增加，即增加横向OLED基板 (1) 与封装基板之间的抗拉力，从而提高OLED面板的稳定性，确保OLED面板的密封效果，提高OLED面板的使用寿命。

